

Features

- Fast Switching Speed
- Low Current Leakage
- Low Cost
- Compression Bond Construction
- Surface Mount Application

Maximum Ratings

- Operation & Storage Temperature: -55°C to +150°C
- Maximum Thermal Resistance: 35°C/W Junction to Ambient

Electrical Characteristics @ 25°C Unless Otherwise Specified

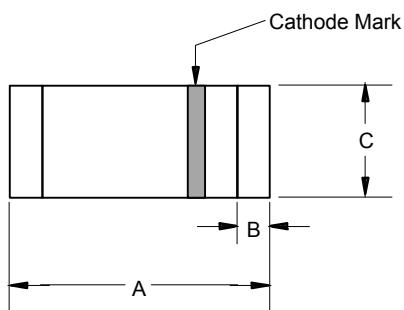
Reverse Volt.	V_R	75V	
Peak Reverse Volt.	V_{RM}	100V	
Average Rectified Current	I_O	150mA	Resistive Load $f>50\text{Hz}$
Power Dissipation	P_{TOT}	500mW	
Junction Temperature	T_J	200°C	
Peak Forward Surge Current	I_{FSM}	500mA	8.3ms, half sine
Maximum Instantaneous Forward Volt.	V_F	1.0V	$I_{FM}=10\text{mA}; T_J=25^\circ\text{C}$
Maximum DC Reverse Current At Rated DC Blocking Voltage	I_R	25nA 50uA	$V_R=20\text{V}$ $T_J=25^\circ\text{C}$ $T_J=150^\circ\text{C}$
Typical Junction Capacitance	C_J	4pF	Measured at 1.0MHz, $V_R=4.0\text{V}$
Reverse Recovery Time	T_{rr}	4nS	$I_F=10\text{mA}$ $V_R=6\text{V}$ $R_L=100 \text{ OHMS}$

Pulse test: Pulse width 300 usec, Duty cycle 2%.

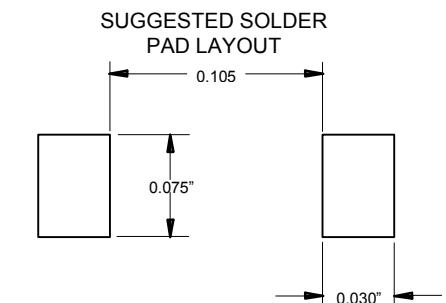
DL914

500mW 100 Volt Silicon Switching Diode

MINIMELF

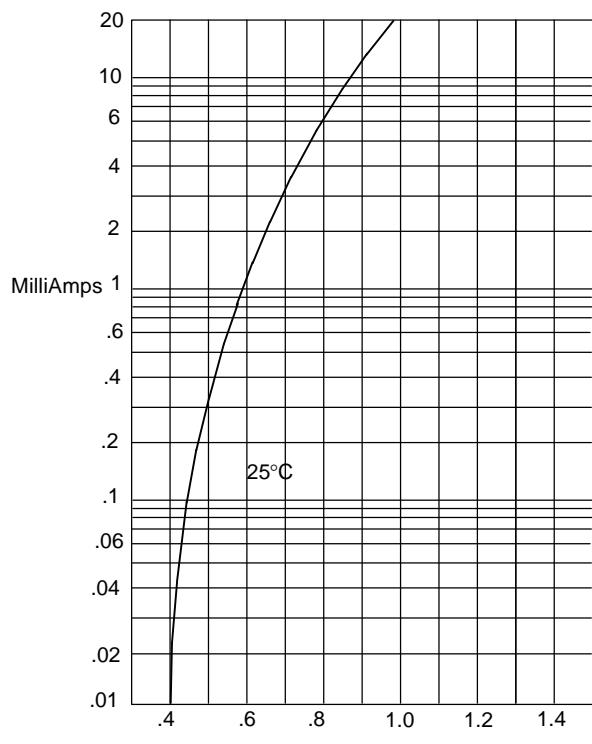


DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.134	.142	3.40	3.60	
B	.008	.016	0.20	0.40	
C	.055	.059	1.40	1.50	



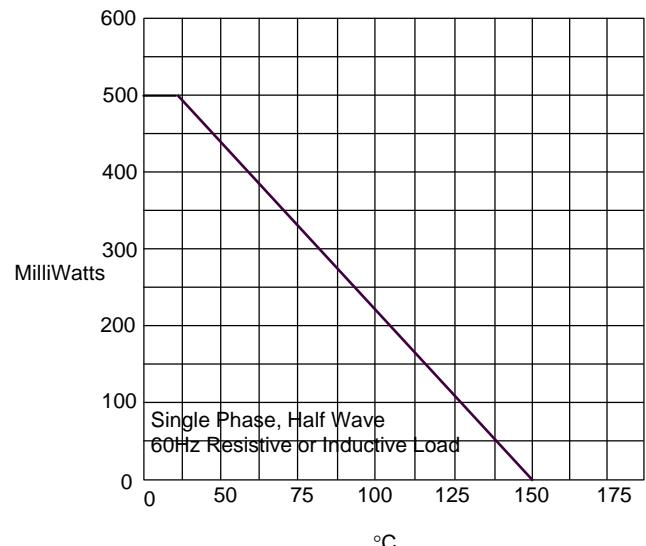
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Figure 1
Typical Forward Characteristics



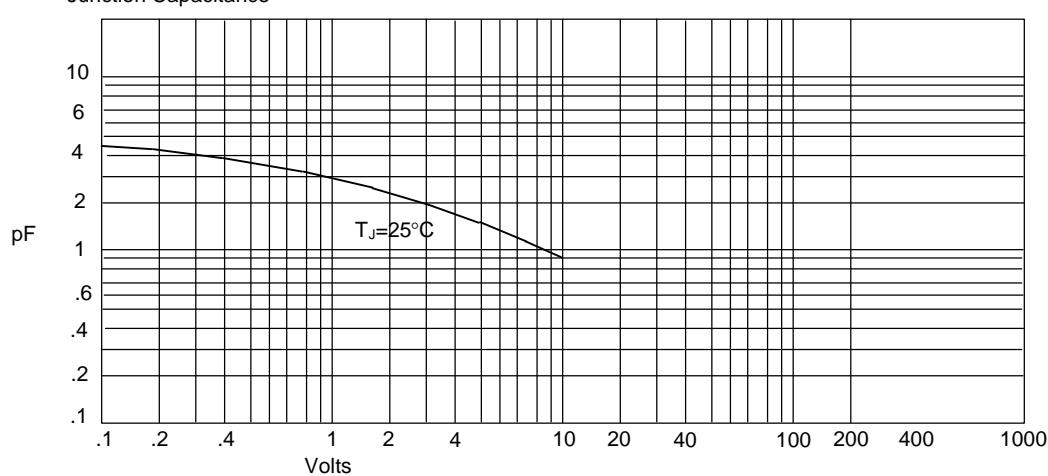
Instantaneous Forward Current - Amperesversus
Instantaneous Forward Voltage - Volts

Figure 2
Forward Derating Curve



Admissible Power Dissipation - Milliwattsversus
Ambient Temperature - °C

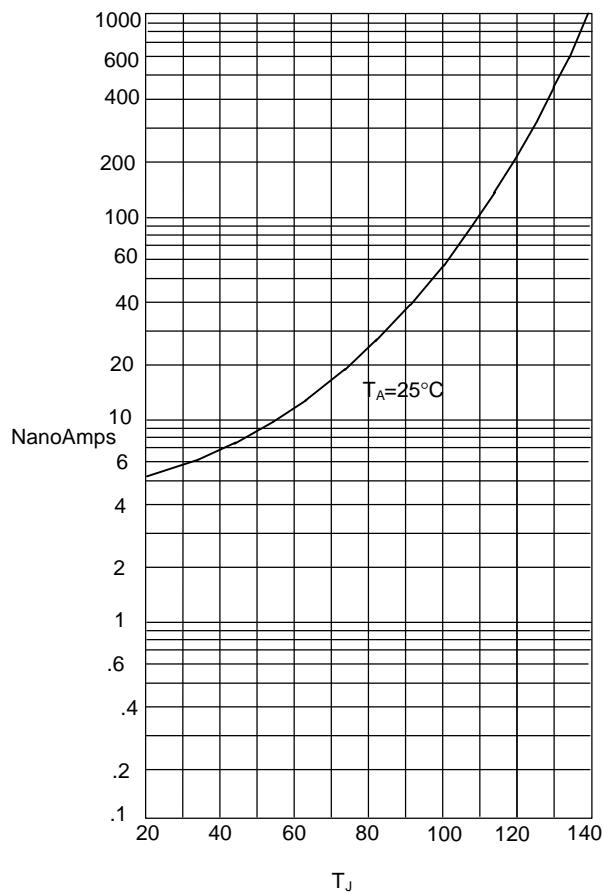
Figure 3
Junction Capacitance



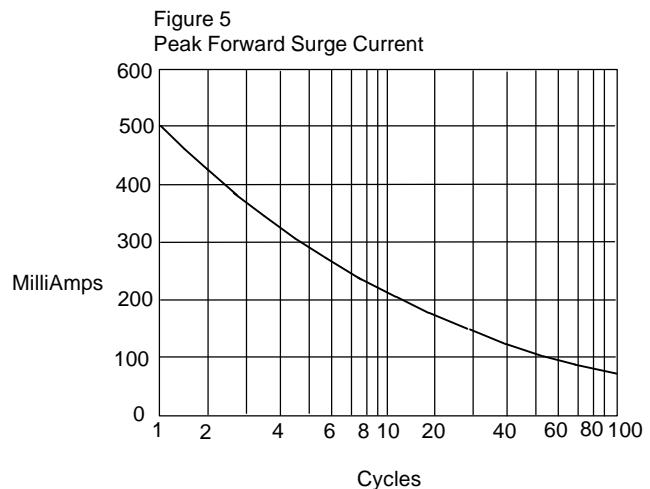
Junction Capacitance - pFversus
Reverse Voltage - Volts

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Figure 4
Typical Reverse Characteristics



Instantaneous Reverse Leakage Current - NanoAmperesversus
Junction Temperature - °C



Peak Forward Surge Current - Amperesversus
Number Of Cycles At 60Hz - Cycles